CLAIMS

1. An Al wiring material containing at least Sc, Zr and Ni so as to satisfy

$$0.01 \leq x1 \leq 0.5,$$

$$0.01 \leq x2 \leq 0.3, \text{ and}$$

$$10 \leq x3 < 200$$

where x1 is a content of Sc [% by weight], x2 is a content of Zr [% by weight] and x3 is a content of Ni [ppm by weight],

with the balance comprising Al,

wherein,

a wire diameter is equal to or larger than 50 μm and equal to or smaller than 600 μm.

2. The Al wiring material according to claim 1, further wherein an average crystal grain diameter at a cross section (C cross section) perpendicular to a wire longitudinal direction is equal to or larger than 1 μm and equal to or smaller than 50 μm.

3. The Al wiring material according to claim 1 or 2, wherein x1 and x2 satisfy a relation of $x2/x1 > 0.5$.

4. The Al wiring material according to any one of claims 1 to 3, wherein Vickers hardness of a longitudinal axis part of the Al wiring material is 40 Hv or less.

5. The Al wiring material according to any one of claims 1 to 4, wherein the Al wiring material has been subjected to a thermal refining heat treatment at 580 to 640°C for 30 seconds or less.

6. The Al wiring material according to any one of claims 1 to 5, wherein the Al wiring material does not have a coating that contains a metal other than Al as a main component.

7. The Al wiring material according to any one of claims 1 to 6, wherein the Al wiring material is a bonding wire.

8. The Al wiring material according to any one of claims 1 to 7, wherein the Al wiring material is subjected to aging heat treatment at 250 to 400°C for 30 to 60 minutes after being connected to a member to be connected.

9. A semiconductor device comprising the Al wiring material according to any one of claims 1 to 8.